

PH20-GE-OD1-D0

Photodiode detector for laser power measurement up to 300 mW.



PRODUCT FAMILY KEY FEATURES

LARGE APERTURES

10 mm Ø for the silicon sensors

3 VERSIONS

- Silicon 350 1080 nm, up to 750 mW
- Silicon-UV 210 1080 nm, up to 38 mW
- Germanium 800 1650 nm, up to 500 mW

CHOICE OF ATTENUATORS

- OD0.3: 50% transmission (for PH100-SI^{UV} only)
- OD1: 10% transmission
- OD2: 1% transmission

HIGH ACCURACY

The new PH100-SI-HA presents the lowest calibration uncertainty to date.

38.1Ø x 36D mm

PRECISE CALIBRATION

Wavelength selection in 1 nm steps

SMART INTERFACE

Containing all the calibration data

COMPATIBLE STAND

STAND-D-233

SPECIFICATIONS

MEASUREMENT CAPABILITIES	
Maximum average power ¹	300 mW
Noise equivalent power ²	600 pW
Spectral range	900 - 1650 nm
Typical rise time	0.2 s
Power calibration uncertainty ³	±5.0 % (900 - 1559 nm) ±7.0 % (1560 - 1629 nm) ±10 % (1630 - 1650 nm)
Peak sensitivity	1550 nm
Minimum repetition rate ⁴	155 kHz
1. At 1064 nm, with attenuator. See curves for maximum power at other wavelengths.	

- 2. At 1550 nm. Nominal value. Actual value depends on environmental electromagnetic interference and wavelength.
- 3. With attenuator. See user manual for calibration uncertainty without attenuator.
- 4. See user manual for details.

Dimensions

100 W/cm² Maximum average power density

PHYSICAL CHARACTERISTICS

Aperture diameter	5 mm
Absorber	Ge

0.14 kg Weight

10.5 mm Distance to sensor face

ORDERING INFORMATION		
PH20-Ge-OD1-D0	200874	
PH20-Ge-OD1-INT-D0	202796	
PH20-Ge-ODI-IDR-D0	203244	

Specifications are subject to change without notice. Refer to the user manual for complete specifications.

INTERESTED IN THIS PRODUCT?



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